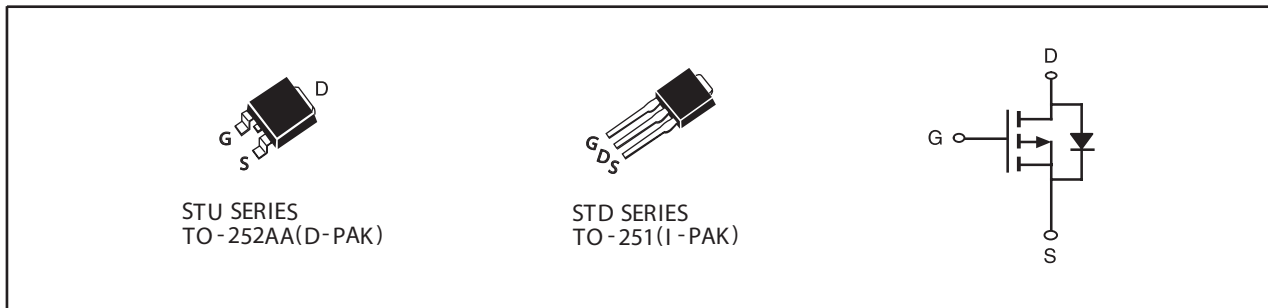


**P-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-40V	-38A	17.5 @ V _{GS} =10V
		27 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.

**ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	-40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	T _C =25°C	-38
		T _C =70°C	-30.4
I _{DM}	-Pulsed ^a	-115	A
E _{AS}	Single Pulse Avalanche Energy ^c	156	mJ
P _D	Maximum Power Dissipation	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θ JC}	Thermal Resistance, Junction-to-Case	3	°C/W
R _{θ JA}	Thermal Resistance, Junction-to-Ambient	50	°C/W

STU/D435S

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-32V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.7	-3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V , I _D =-19A		14	17.5	m ohm
		V _{GS} =-4.5V , I _D =-15A		20	27	m ohm
g _{FS}	Forward Transconductance	V _{DS} =-10V , I _D =-19A		36		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V f=1.0MHz		1950		pF
C _{OSS}	Output Capacitance			229		pF
C _{RSS}	Reverse Transfer Capacitance			186		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =-20V I _D =-1A V _{GS} =-10V R _{GEN} = 6 ohm		24		ns
t _r	Rise Time			38		ns
t _{D(OFF)}	Turn-Off Delay Time			11		ns
t _f	Fall Time			8		ns
Q _g	Total Gate Charge	V _{DS} =-20V, I _D =-19A, V _{GS} =-10V		42		nC
		V _{DS} =-20V, I _D =-19A, V _{GS} =-4.5V		20		nC
Q _{gs}	Gate-Source Charge	V _{DS} =-20V, I _D =-19A, V _{GS} =-10V		3.4		nC
Q _{gd}	Gate-Drain Charge			11		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S = -4A		-0.78	-1.3	V

Notes

- a. Pulse Test: Pulse Width < 300us, Duty Cycle < 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Starting T_J=25°C, L=0.5mH, V_{DD} = 20V .(See Figure13)

Jul,01,2011

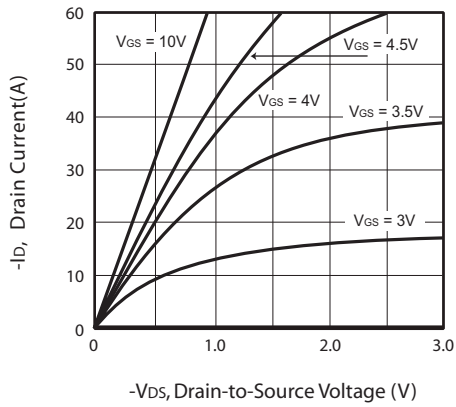


Figure 1. Output Characteristics

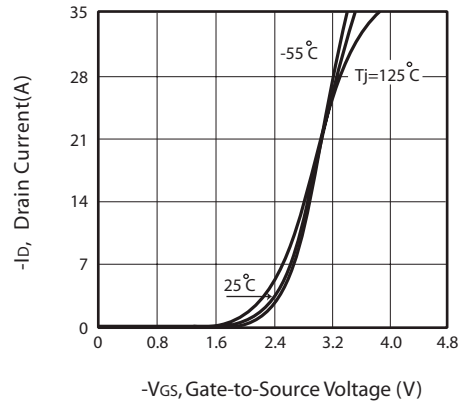


Figure 2. Transfer Characteristics

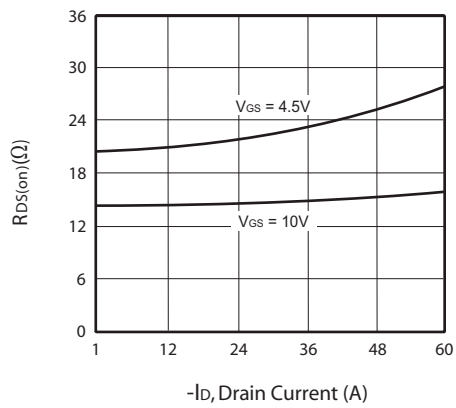


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

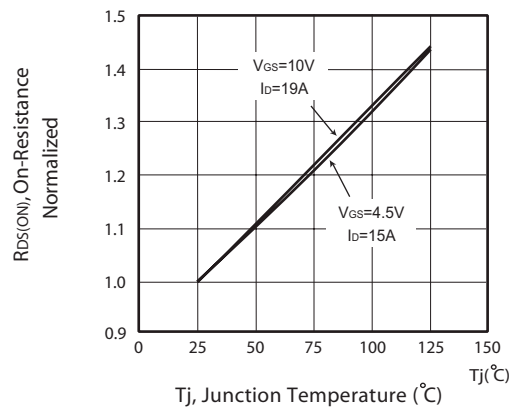


Figure 4. On-Resistance Variation with Drain Current and Temperature

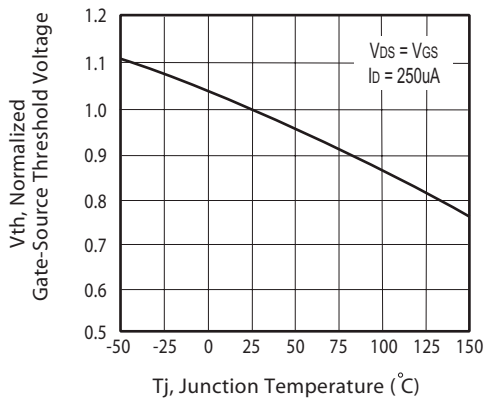


Figure 5. Gate Threshold Variation with Temperature

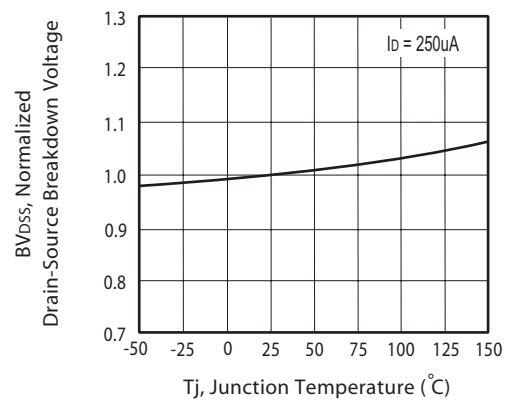


Figure 6. Breakdown Voltage Variation with Temperature

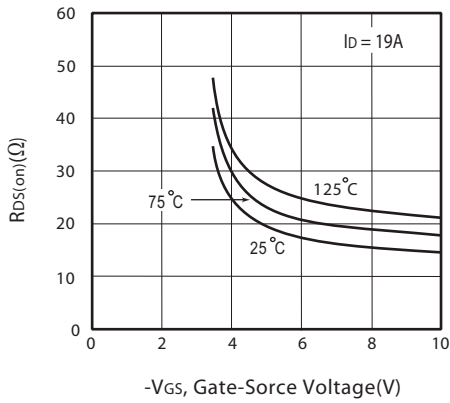


Figure 7. On-Resistance vs. Gate-Source Voltage

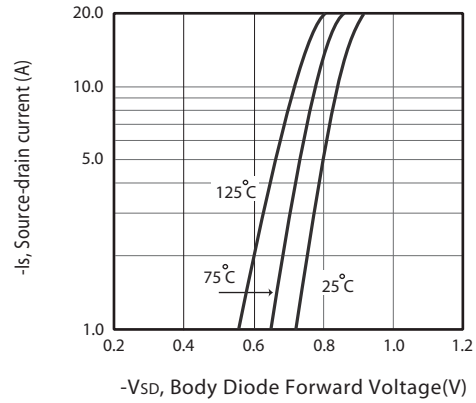


Figure 8. Body Diode Forward Voltage Variation with Source Current

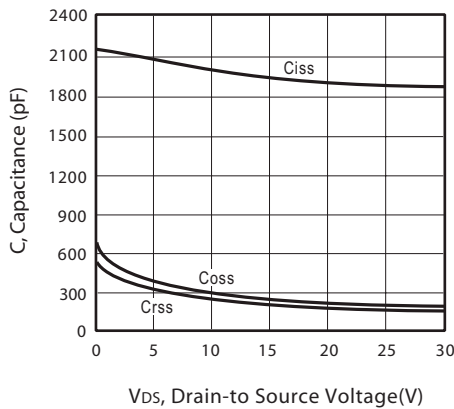


Figure 9. Capacitance

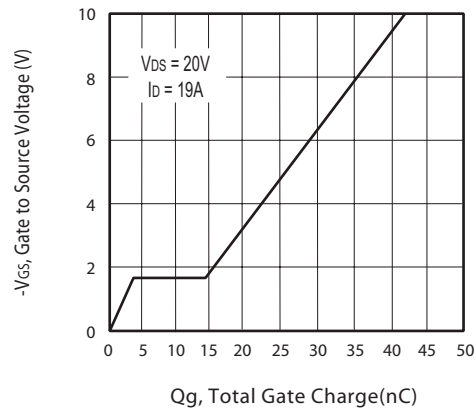


Figure 10. Gate Charge

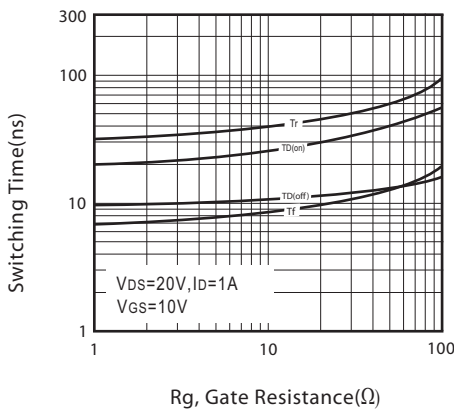


Figure 11. switching characteristics

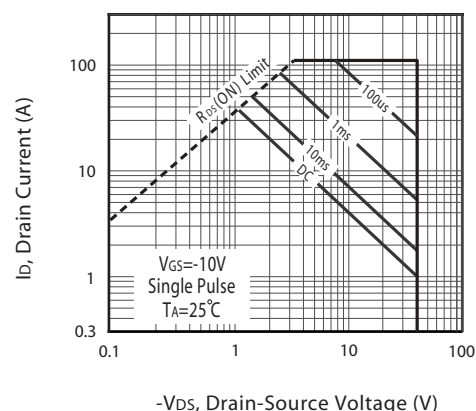
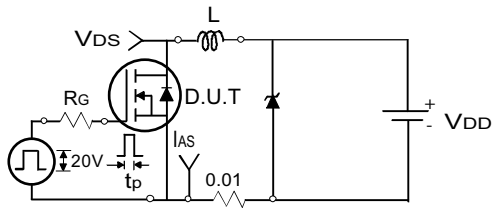
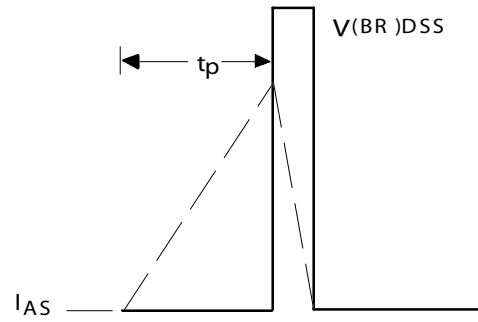


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

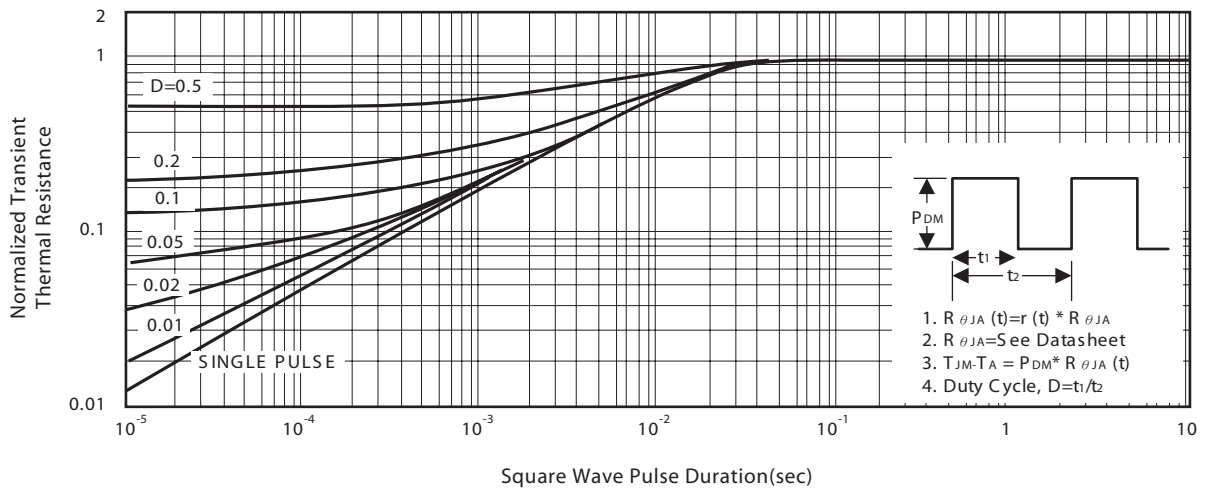
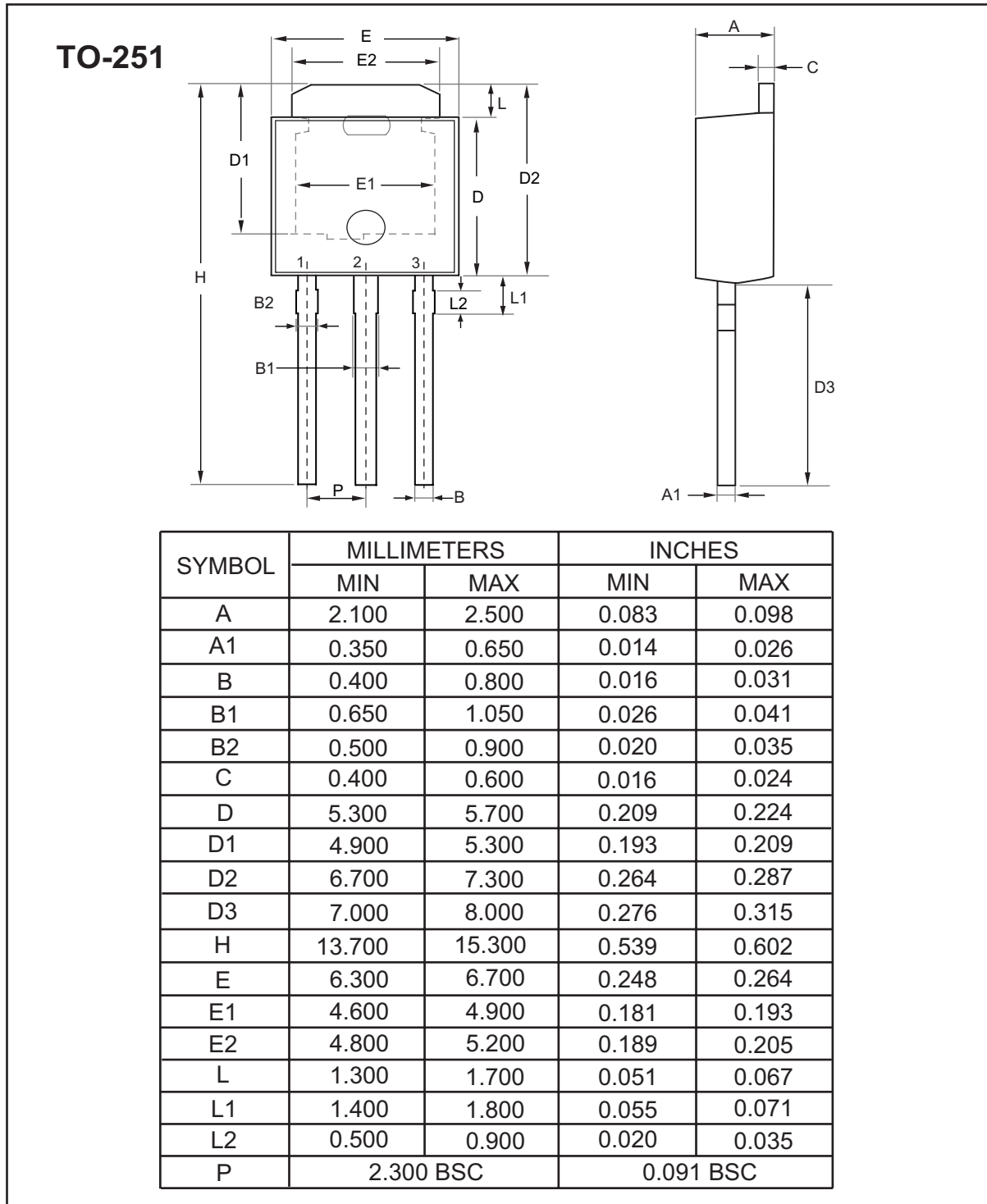


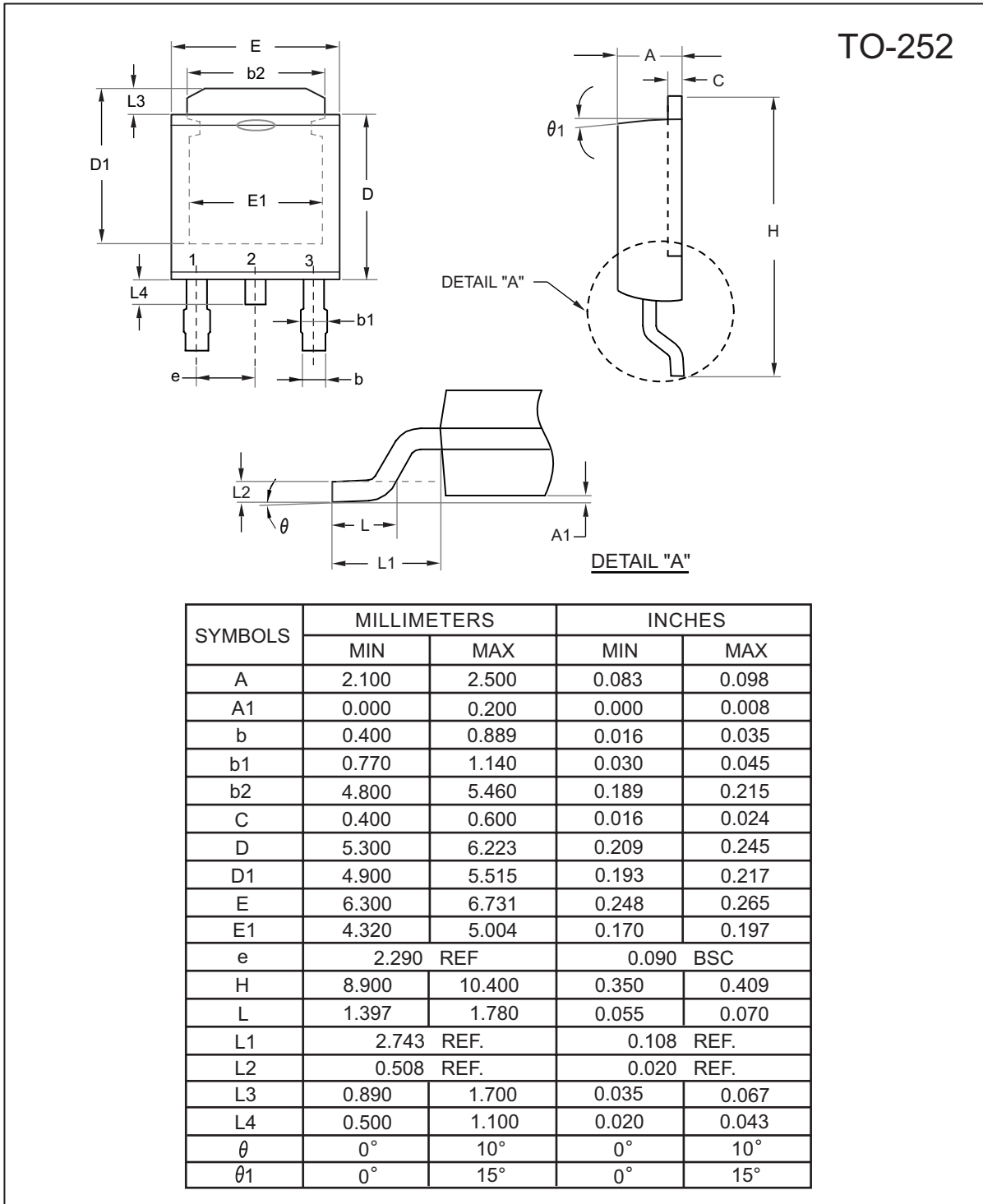
Figure 14. Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS



STU/D435S

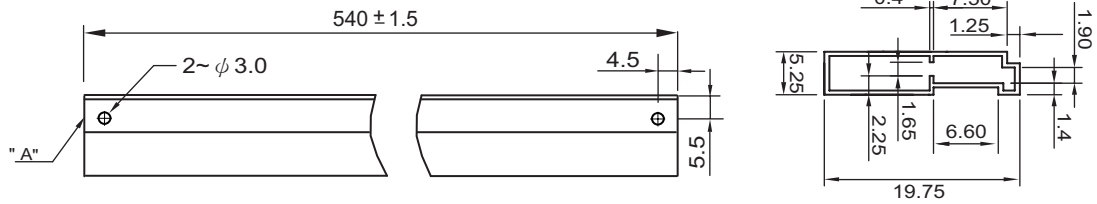
Ver 1.0



Jul,01,2011

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



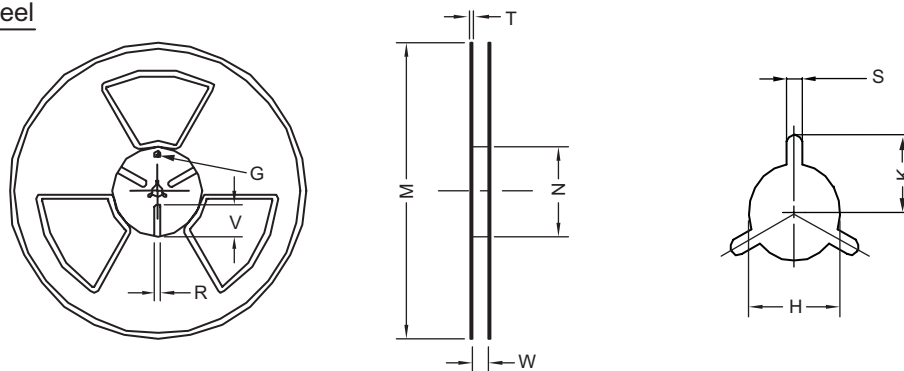
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---